

PATENT APPLICATION
DOCKET NO. PDNO. 10010430-1
47429-00038USPT

In the Claims

1 12. (previously presented) A Bragg reflector comprising:
2 one or more first layers adjacent one or more second layers, the first and second layers
3 having at least one sidewall, wherein the first and second layers define one or more gaps; and
4 a support layer formed over a portion of the sidewalls to support the second layers
5 against collapse into the one or more gaps.

1 13. (original) The Bragg reflector of claim 12 wherein the second layers and the
2 support layer comprise substantially the same material.

1 14. (original) The Bragg reflector of claim 12 wherein at least a portion of the
2 support layer is electrically conductive.

1 15. (previously presented) The Bragg reflector of claim 12 wherein a portion of the
2 support layer is electrically non-conductive.

1 16. (original) A distributed Bragg reflector comprising:
2 a substrate;
3 a plurality structure layers on the substrate each spaced apart by a gap, the
4 structure layers each having edges; and
5 a support layer about a portion of the edges for supporting the structure layers.

PATENT APPLICATION
DOCKET NO. F'DNO. 10010430-1
47429-00038USPT

1 17. (original) The distributed Bragg reflector of claim 16 further comprising
2 sacrificial layers between the structure layers, the sacrificial layers undercut to define the
3 gaps.

1 18. (original) The distributed Bragg reflector of claim 16 wherein the support layer
2 comprises a material selected from the group consisting of InP, GaAs, and Si.

1 19. (original) The distributed Bragg reflector of claim 16 wherein the structure layers
2 comprise a material selected from the group consisting of InP, GaAs, and Si

1 20. (original) The distributed Bragg reflector of claim 16 wherein the support layer
2 covers at least a portion of a top of the structure layers.